

Sub
A7

[illegible]

- semiconductor device comprising:
provided on a semiconductor substrate
line conductors provided on said ground
interlayer insulation films intervening therebetween
on most upper one of said interlayer insulation films
provided in said most upper one of said interlayer insulation films
line conductor on said most upper one of said interlayer insulation films
semiconductor device as set forth in claim 1
pad.
semiconductor device as set forth in claim 1
between said pad and said line conductor
films.
semiconductor device as set forth in claim 3
on along an edge of said semiconductor substrate
on on said semiconductor substrate extending
semiconductor device as set forth in claim 3,
most upper one of said interlayer insulation films
semiconductor device as set forth in claim 1,
one of said interlayer insulation films on said semiconductor substrate
to a potential via said through-hole.
semiconductor device as set forth in claim 1 in
most upper one of said interlayer insulation films

8. A high-frequency semiconductor device as set forth in claim 1, wherein said groove is provided to have a ring shape within said semiconductor substrate, and said pad is provided on said most upper one of said interlayer insulation films outside said ring shaped groove.

add B1

[illegible]